



DMT2004UFG

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
	5.0mΩ @ V _{GS} = 10V	70A
24V	6.5mΩ @ V _{GS} = 4.5V	60A
	10.0mΩ @ V _{GS} = 2.5V	45A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

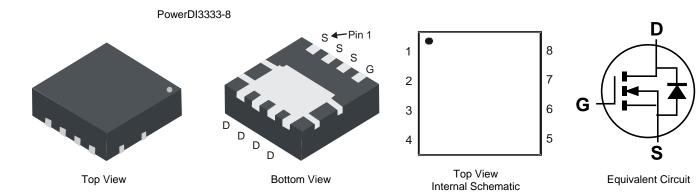
N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Features and Benefits

- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ^(G)
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMT2004UFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT2004UFG-13	PowerDI3333-8	3,000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



SF2 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 16 = 2016) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	24	V		
Gate-Source Voltage	V _{GSS}	±12	V		
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	ID	70 55	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	90	A
Continuous Source-Drain Diode Current (Note 6)			ls	2.5	A
Avalanche Current (Note 8) L = 0.1mH			I _{AS}	26	A
Avalanche Energy (Note 8) L = 0.1mH			E _{AS}	36	mJ

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	106	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	54	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _θ JC	3.5	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

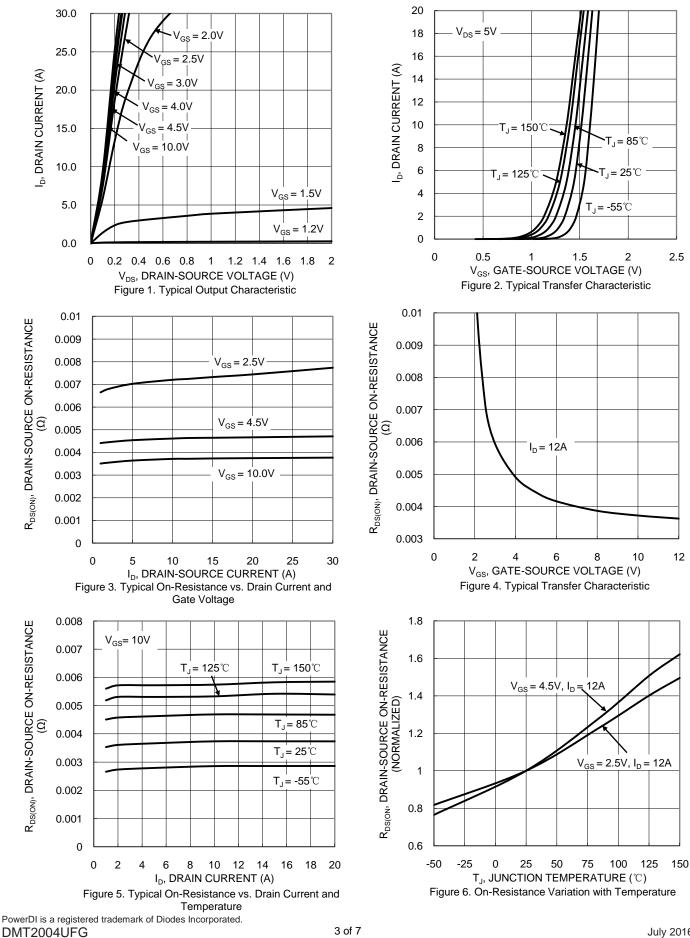
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	Symbol	IVIIII	тур	IVIAX	Unit	Test condition	
Drain-Source Breakdown Voltage	BV _{DSS}	24			V	$V_{GS} = 0V, I_{D} = 250 \mu A$	
Zero Gate Voltage Drain Current ($T_J = +25^{\circ}C$)	IDSS	_	_	1	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 10V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	000						
Gate Threshold Voltage	V _{GS(TH)}	0.55		1.45	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		—	3.7	5.0		$V_{GS} = 10V, I_D = 12A$	
Static Drain-Source On-Resistance	RDS(ON)	—	4.5	6.5	mΩ	V _{GS} = 4.5V, I _D = 12A	
		—	7.5	10.0		$V_{GS} = 2.5V, I_D = 12A$	
Diode Forward Voltage	V _{SD}	—	0.65	1.0	V	$V_{GS} = 0V, I_S = 2A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	-	1683	—			
Output Capacitance	Coss	_	581	—	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	—	559	—			
Gate Resistance	R _G	_	1.6	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	29.6	_		V _{DD} = 15V, I _D = 9A	
Total Gate Charge (V _{GS} = 10V)	Qg	—	53.7	—	nC		
Gate-Source Charge	Q _{gs}	_	4.2	—	nc		
Gate-Drain Charge	Q _{gd}	—	13.4	—			
Turn-On Delay Time	t _{D(ON)}	_	3.9	—			
Turn-On Rise Time	t _R	—	9.6	—		$V_{DD} = 15V, V_{GS} = 10V,$ $R_G = 3\Omega, I_D = 9A$	
Turn-Off Delay Time	t _{D(OFF)}	_	30.8	—	ns		
Turn-Off Fall Time	tF	—	38.6				
Reverse Recovery Time	t _{RR}	—	11.2		ns		
Reverse Recovery Charge	Q _{RR}	—	22.9		nC	I _F = 1.5A, di/dt = 100A/µs	

Notes:

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

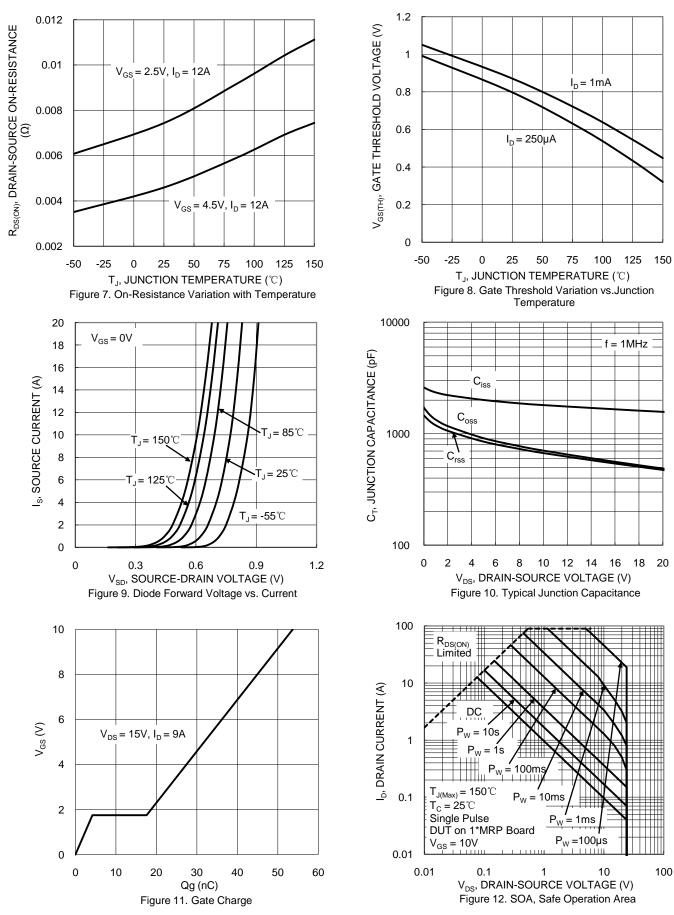


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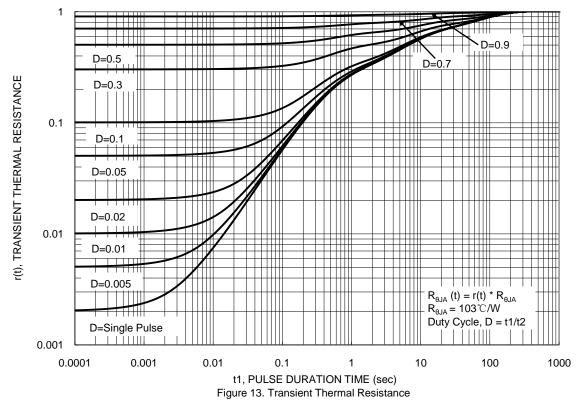
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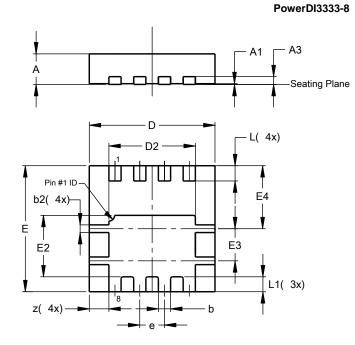






Package Outline Dimensions

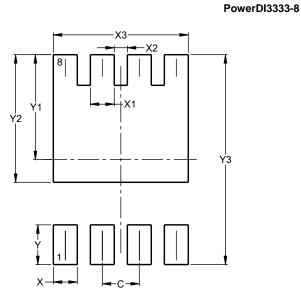
Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	1	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	-	-	0.65			
L	0.35	0.45	0.40			
L1	_	-	0.39			
z	_	_	0.515			
All I	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230 2.370		
X3			
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		

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